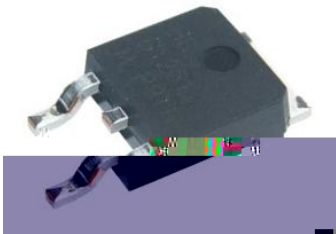
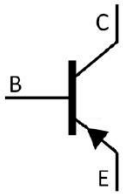


Silicon PNP transistor in a TO-252 Plastic Package.

Complement to MJD41C.

Medium power linear switching applications.

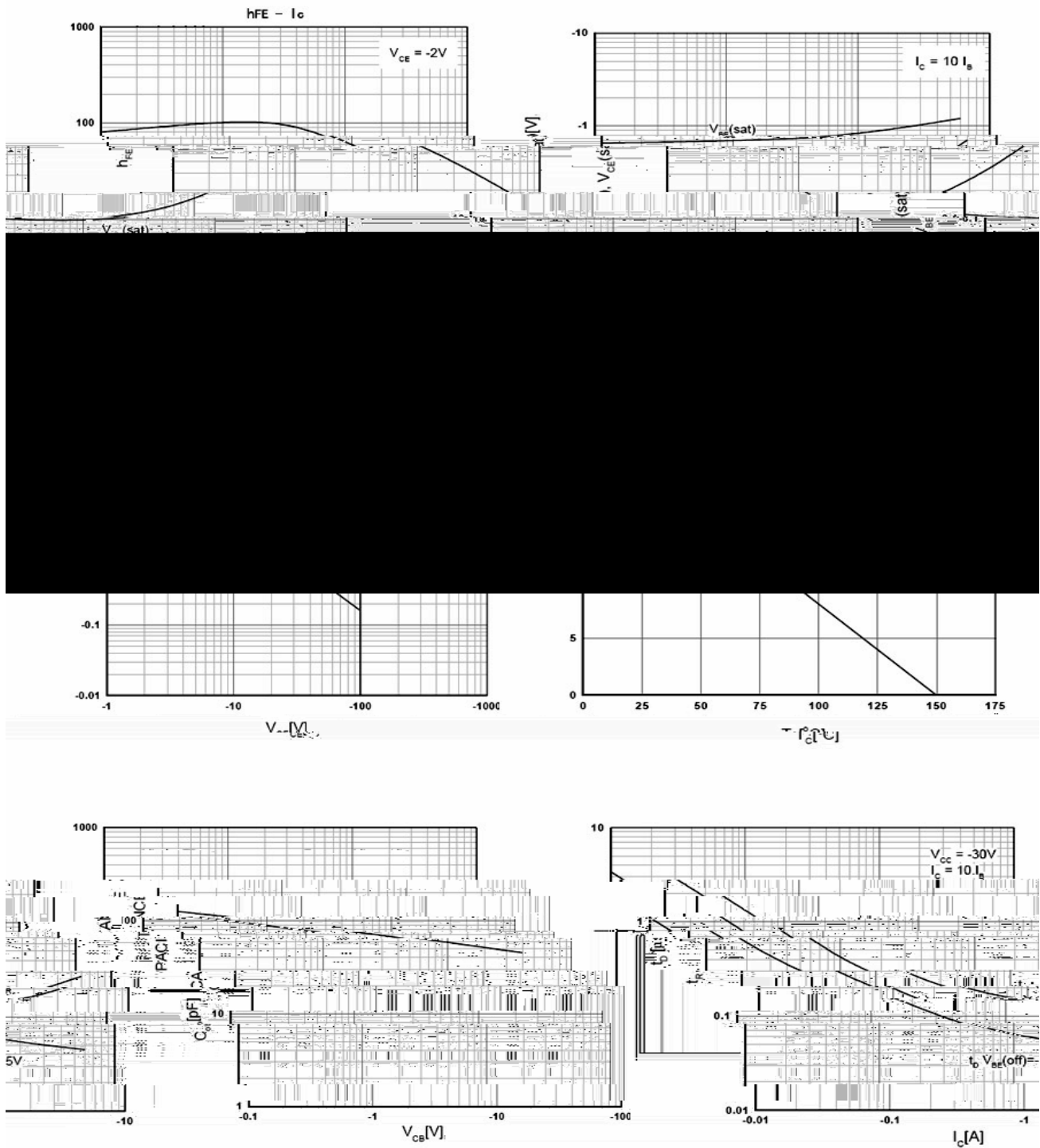


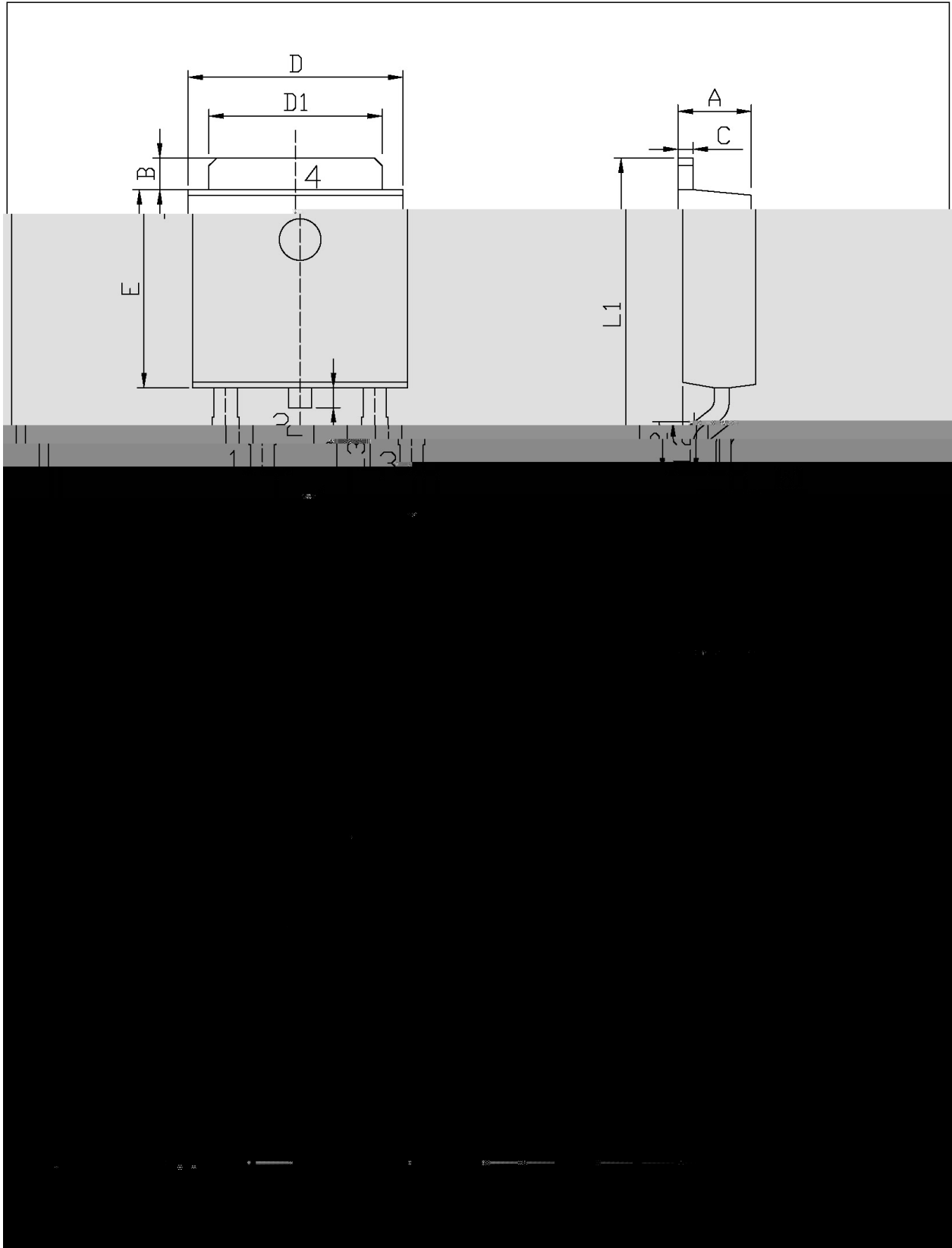
PIN1	Base	PIN 2,4	Collector	PIN 3	Emitter
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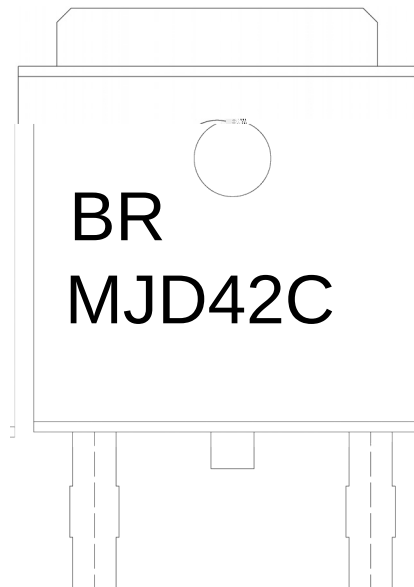
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-100	V
Collector to Emitter Voltage	V_{CEO}	-100	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-6.0	A
Base Current - Continuous	I_B	-2.0	A
Collector Power Dissipation	P_D	1.75	W
Collector Power Dissipation	$P_D(T_C=25^\circ\text{C})$	20	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55~150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-30\text{mA}$ $I_B=0$	-100			V
Collector Cut-Off Current	I_{CEO}	$V_{CE}=-60\text{V}$ $I_B=0$			-50	A
Collector Cut-Off Current	I_{CES}	$V_{CE}=-100\text{V}$ $V_{BE}=0$			-10	A
Emitter Cut-Off Current	I_E					







BR

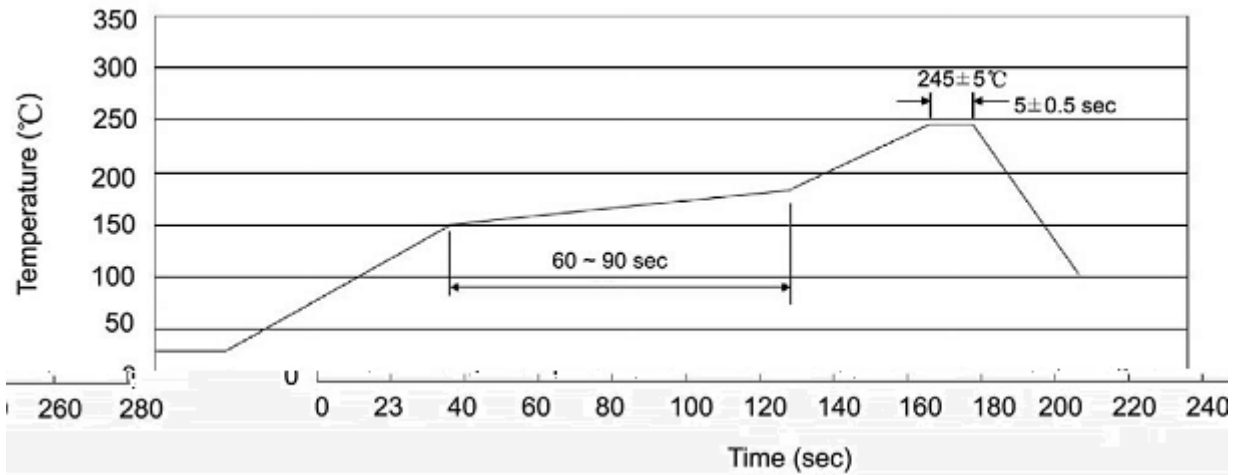
Note:

BR: Company Code

MJD42C: Product Type.

****: Lot No. Code, code change with Lot No.

Temperature Profile for IR Reflow Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 245 | 5 | 5 | 0.5sec; | 2.Peak Temp.:245 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

260 5 10 1 sec. Temp.:260±5 Time:10±1 sec

/ REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱
						"		

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱